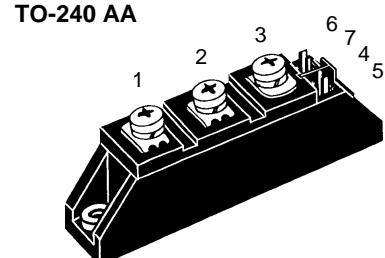
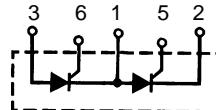


# Thyristor Modules

$V_{RSM}$	$V_{RRM}$	Type
$V_{DSM}$	$V_{DRM}$	
V	V	
900	800	MCC 21-08io8 B
1300	1200	MCC 21-12io8 B
1500	1400	MCC 21-14io8 B
1700	1600	MCC 21-16io8 B



Symbol	Conditions	Maximum Ratings		
$I_{TRMS}$	$T_{VJ} = T_{VJM}$	33	A	
$I_{TAVM}$	$T_C = 85^\circ\text{C}$ ; 180° sine	21	A	
$I_{TSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $V_R = 0$	320 350	A A	
	$T_{VJ} = T_{VJM}$ $V_R = 0$	280 310	A A	
$I^2dt$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	500 520	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$	
	$T_{VJ} = T_{VJM}$ $V_R = 0$	390 400	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$	
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50\text{Hz}$ , $t_p = 200\mu\text{s}$	repetitive, $I_T = 45\text{ A}$	150	$\text{A}/\mu\text{s}$
	$V_D = \frac{2}{3} V_{DRM}$ $I_G = 0.45\text{ A}$ $di_G/dt = 0.45\text{ A}/\mu\text{s}$		500	$\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$ ; $V_{DR} = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)		1000	$\text{V}/\mu\text{s}$
$P_{GM}$	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30\mu\text{s}$ $t_p = 300\mu\text{s}$	10 5	W W
$P_{GAV}$			0.5	W
$V_{RGM}$			10	V
$T_{VJ}$			-40...+125	$^\circ\text{C}$
$T_{VJM}$			125	$^\circ\text{C}$
$T_{stg}$			-40...+125	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1\text{ mA}$	$t = 1\text{ min}$ $t = 1\text{ s}$	3000 3600	$\text{V}\sim$ $\text{V}\sim$
$M_d$	Mounting torque (M5) Terminal connection torque (M5)		2.5-4.0/22-35 Nm/lb.in. 2.5-4.0/22-35 Nm/lb.in.	
<b>Weight</b>	Typical including screws		90	g

Data according to DIN/IEC 747 and refer to a single thyristor unless otherwise stated.

Symbol	Conditions	Characteristic Values		
$I_{RRM}, I_{DRM}$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	5	mA	
$V_T$	$I_T = 45 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.6	V	
$\frac{V_{TO}}{r_T}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )	0.85 15	V $\text{m}\Omega$	
$V_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	1.0 1.2	V V	
$I_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	65 80	mA mA	
$\frac{V_{GD}}{I_{GD}}$	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	0.2 5	V mA	
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	150	mA	
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	100	mA	
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	2	$\mu\text{s}$	
$t_q$	$T_{VJ} = T_{VJM}; I_T = 15 \text{ A}, t_p = 300 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = \frac{2}{3} V_{DRM}$	typ.	150	$\mu\text{s}$
$I_{RM}$	$T_{VJ} = T_{VJM}; I_T = 30 \text{ A}, -di/dt = 0.3 \text{ A}/\mu\text{s}$	4	A	
$R_{thJC}$	per thyristor; DC current	other values see Fig. 8/9	1.1	K/W
	per module		0.55	K/W
$R_{thJK}$	per thyristor; DC current		1.3	K/W
	per module		0.65	K/W
$d_s$	Creepage distance on surface	12.7	mm	
$d_A$	Strike distance through air	9.6	mm	
$a$	Maximum allowable acceleration	50	$\text{m/s}^2$	

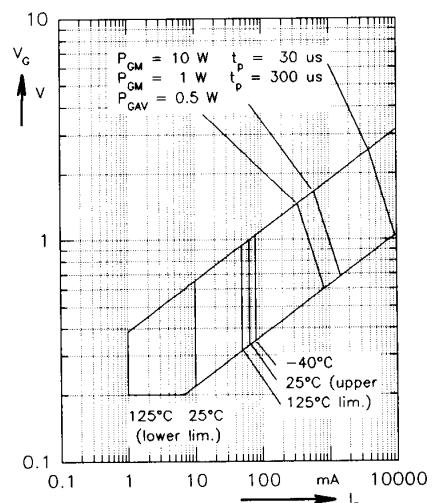


Fig. 1 Gate trigger characteristics

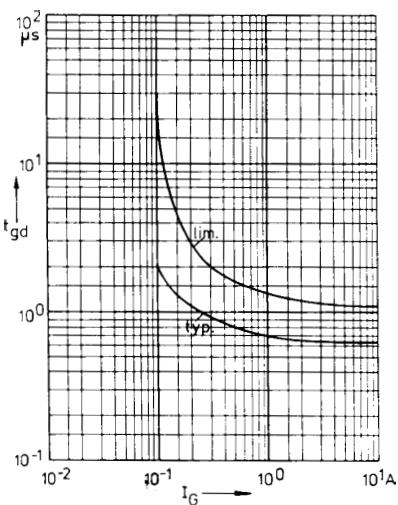


Fig. 2 Gate trigger delay time

**Dimensions in mm (1 mm = 0.0394")**

